AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Please replace the title of with the following title:

METHOD OF MAKING BONDED WAFER WITH FITTING SURFACE

Please replace paragraph [0009] and the unnumbered paragraphs following, appearing at page 4, with the following amended paragraphs:

[0009] A second invention provides a manufacturing method of a bonded wafer as defined in the first invention, in which at least either one of the fitting surface of the active layer wafer [[and]] or the fitting surface of the supporting wafer includes a hetero structure along a thickness-wise direction.

The hetero structure refers to a structure containing different types of substance in contact with each other at the site of a certain interface. The area proximal to the interface between the different types of substance defines a hetero junction of two phases having a lattice structure, a chemical composition and a thermal expansion coefficient that are different from each other. Accordingly, a stress acts on the hetero junction, and so a strain will be induced therein. Owing to this strain, a warp (deformation) is generated in the wafer having the hetero structure.

Further, those different types of substance include a combination of the same substances exclusively having different dopant concentrations, a monocrystal silicon and a polycrystal silicon, a bulk substance and an oxide film of the wafer, or a wafer bulk substance and a nitride film, for example.

It is to be noted that the wafer subject to the arrangement of the hetero structure may be the active layer wafer or the supporting wafer. Alternatively, both of the active layer wafer and the supporting wafer may be provided with the hetero structure.

Please replace paragraph [0011] and the unnumbered paragraphs following, appearing at page 6, with the following amended paragraph:

[0011] A third invention provides a manufacturing method of a bonded wafer as defined in the second invention, in which the hetero structure is provided along the thickness-wise direction in the epitaxial growth method.

The epitaxial growth method includes the vapor phase epitaxial growth method, the liquid phase epitaxial growth method and the solid phase epitaxial growth method. The vapor epitaxial growth method includes a chemical method (CVD method: Chemical Vapor Deposition) and a physical method (PVD method: Physical Vapor Deposition).

Accordingly, the hetero structure may be constructed by growing the monocrystal silicon epitaxially and/or by depositing the film of polycrystal silicon in the CVD method, for example. If the above-discussed film is deposited over the top and back surfaces of at least either one of the active layer wafer [[and]] or the supporting wafer, the wafer will be curved (to warp) due to the thermal expansion constant or the chemical reaction.

Please replace paragraph [0013], appearing at page 7, with the following amended paragraph:

A fourth invention provides a manufacturing method of a bonded wafer as defined in the first invention, in which at least either one of the fitting surface of the active layer wafer [[and]]

or the fitting surface of the supporting wafer includes an insulating film along a thickness-wise direction.